L Number	Hits	Search Text	DB	Time stamp
1	1589	stress near3 buffer	USPAT;	2004/10/28 17:18
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	6639	dual near3 (damacene damascene)	USPAT;	2004/10/28 17:18
-	0000		US-PGPUB;	250 17 10/20 11:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	43955	spin?coat\$3 spin adj coat\$3	USPAT;	2004/10/28 17:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	00000		IBM_TDB	0004440400 477.40
5	20296	semiconductor and planarization	USPAT;	2004/10/28 17:18
ا ء	786	/comisonal sates and planarization) and substantially addition	US-PGPUB	0004/40/00 47.40
6	/00	(semiconductor and planarization) and substantially adj flat	USPAT; US-PGPUB	2004/10/28 17:18
7	178	((semiconductor and planarization) and substantially adj flat) and recess	USPAT;	2004/10/28 17:18
'	170	((Semiconductor and plantalization) and substantially adjulate and recess	US-PGPUB	2004/10/20 17.18
15	1836	dual near3 (damacene damascene) and @pd>20031203	USPAT;	2004/10/28 17:18
		:	US-PGPUB;	2001/10/2011/10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	1155	((427/240,385.5) or (257/510,520,621,622,752,774) or	USPAT;	2004/10/28 17:18
		(438/591,623,626,631,677,685)).CCLS. and @pd>20031203	US-PGPUB	
17	19479	spin?coat\$3 spin adj coat\$3 and @pd>20031203	USPAT;	2004/10/28 17:18
			US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
18	208	stress near3 buffer and @pd>20031203	IBM_TDB USPAT;	2004/10/28 17:18
	200	Siless fieals bullet and @pd-20051205	US-PGPUB;	2004/10/20 17.10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	1	(*6461932*).PN.	USPAT;	2004/10/28 17:18
			US-PGPUB	
8	1	(*5663090*).PN.	USPAT;	2004/10/28 17:18
9		(100-0-00) Tu	US-PGPUB	
	1	(*6358793*).PN.	USPAT;	2004/10/28 17:18
10		(/AE AGE 0408) at /BC 4.4C OCOR) at /BC 000 7448) at /BC 005 COER) at /BC 000 4008) at	US-PGPUB .	000440400 47.40
10	6	(("5,405,813") or ("6,146,968") or ("6,228,711") or ("6,235,605") or ("6,303,430") or ("6,417,066")).PN.	USPAT	2004/10/28 17:18
11	2	((3,417,000)).PN. ((("5,405,813") or ("6,146,968") or ("6,228,711") or ("6,235,605") or ("6,303,430") or	USPAT;	2004/10/28 17:18
'	-	(((0,400,613)) ((0,140,908)) ((0,226,711)) ((0,235,005)) ((0,505,430)) ((0,6417,066))).PN.) and (planar flat)	US-PGPUB	2004/10/20 17:10
12	24	((semiconductor and planarization) and substantially adj flat) and substrate near4 recess	USPAT;	2004/10/28 17:18
	- '	The state of the process and process of the state of the	US-PGPUB	2007/10/20 17,10
13	8	(("6278153") or ("6,117,486") or ("6,228,711") or ("6,461,932") or ("2,538,878") or	USPAT;	2004/10/28 17:18
		(*5,677,001*) or (*6,046,083*) or (*6,326,282*)).PN.	US-PGPUB	
14	5	okada and mask and asperity	USPAT;	2004/10/28 17:18
			US-PGPUB	